LINEAR SYSTEMS

Linear Integrated Systems

LS3550 SERIES

MONOLITHIC DUAL PNP TRANSISTORS

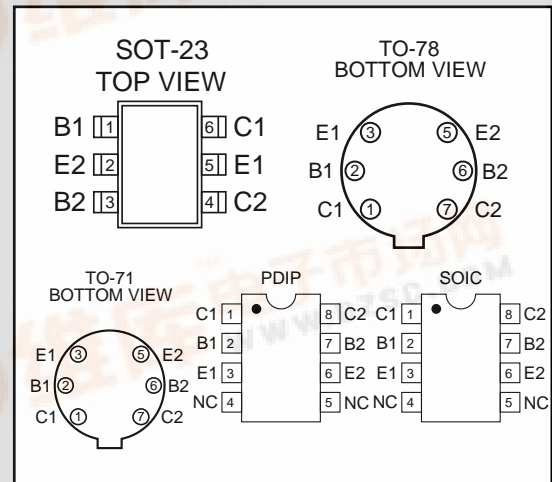| FEATURES	
6 LEAD SOT-23 SURFACE MOUNT PACKAGE*	
TIGHT MATCHING[1]	2mV
EXCELLENT THERMAL TRACKING[1]	3µV/°C
ABSOLUTE MAXIMUM RATINGS[2] @ 25 °C (unless otherwise stated)	
Maximum Temperatures	
Storage Temperature	-65 to +150 °C
Operating Junction Temperature	-55 to +150 °C
Maximum Power Dissipation	
Continuous Power Dissipation	TBD
Maximum Currents	
Collector Current	50mA
Maximum Voltages	
Collector to Collector Voltage	80V

SOT-23 TOP VIEW

TO-78 BOTTOM VIEW

TO-71 BOTTOM VIEW   PDIP   SOIC

MATCHING ELECTRICAL CHARACTERISTICS @25 °C (unless otherwise stated)

	CHARACTERISTIC	LS3250A						UNIT	CONDITIONS
		MIN	MAX	MIN	MAX	MIN	MAX		
$\lvert V_{BE1} - V_{BE2}\rvert$	Base to Emitter Voltage Differential		2		5		10	mV	$I_C = -10mA$, $V_{CE} = -5V$
$\dfrac{\lvert V_{BE1} - V_{BE2}\rvert}{\Delta T}$	Base to Emitter Voltage Differential Change with Temperature		3		5		15	µV/°C	$I_C = -10mA$, $V_{CE} = -5V$ $T_A = -40°C$ to $+85°C$
$\lvert I_{B1} - I_{B2}\rvert$	Base Current Differential		10		10		10	nA	$I_C = -10µA$, $V_{CE} = -5V$
$\dfrac{\lvert I_{B1} - I_{B2}\rvert}{\Delta T}$	Base Current Differential Change with Temperature		0.5		0.5		1.0	nA/°C	$I_C = -10µA$, $V_{CE} = -5V$ $T_A = -40°C$ to $+85°C$
h_{FE1}/h_{FE2}	Current Gain Differential		10		10		15	%	$I_C = -10µA$, $V_{CE} = -5V$

ELECTRICAL CHARACTERISTICS @25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	LS3250A		LS3250B		LS3250C		UNIT	CONDITIONS
		MIN	MAX	MIN	MAX	MIN	MAX		
BV_{CBO}	Collector to Base Breakdown Voltage	-45		-40		-20		V	$I_C = -10mA$, $I_E = 0A$
BV_{CEO}	Collector to Emitter Breakdown Voltage	-45		-40		-20			$I_C = -10µA$, $I_E = 0A$
BV_{CCO}	Collector to Collector Breakdown Voltage	-80		-80		-80			
BV_{EBO}	Emitter to Base Breakdown Voltage[3]	-6.2		-6.2		-6.2			$I_E = -10µA$, $I_C = 0A$
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage		-0.25		-0.25		-1.2		$I_C = -100mA$ $I_B = -10mA$

ELECTRICAL CHARACTERISTICS CONT. @25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	LS3250A MIN	LS3250A MAX	LS3250B MIN	LS3250B MAX	LS3250C MIN	LS3250C MAX	UNIT	CONDITIONS
h_{FE}	DC Current Gain	150		100		50			I_C = -1mA, V_{CE} = -5V
		120		80		40			I_C = -10mA, V_{CE} = -5V
		100		80		40			I_C = -100mA, V_{CE} = -5V
I_{CBO}	Collector Cutoff Current		-0.2		-0.2			nA	I_E = 0A, V_{CB} = -30V
							-0.2		I_E = 0A, V_{CB} = -20V
I_{EBO}	Emitter Cutoff Current		-0.2		-0.2		-0.2		I_E = 0A, V_{CB} = -3V
I_{C1C2}	Collector to Collector Leakage Current		-1		-1		-1		V_{CC} = ±80V
C_{OBO}	Output Capacitance		2		2		2	pF	I_E = 0A, V_{CB} = -10V
f_T	Gain Bandwidth Product (Current)		600		600		600	MHz	I_C = -1mA, V_{CE} = -5V
NF	Noise Figure (Narrow Band)		3		3		3	dB	I_C = -100µA, V_{CE} = -5V BW = 200Hz R_B = 10Ω, f = 1kHz
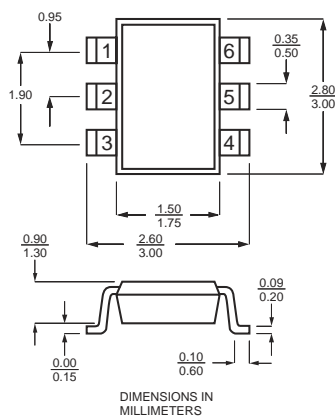
SOT-23

TO-71
Six Lead

TO-78

PDIP

SOIC

DIMENSIONS IN MILLIMETERS

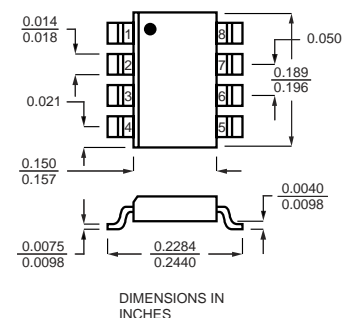DIMENSIONS IN INCHES
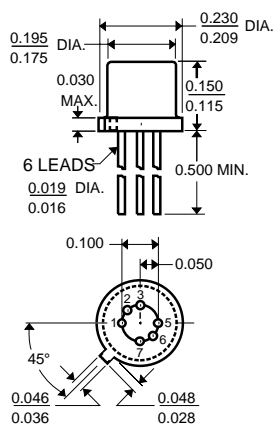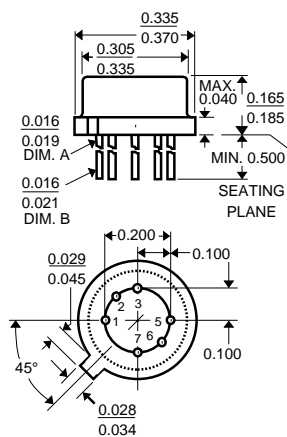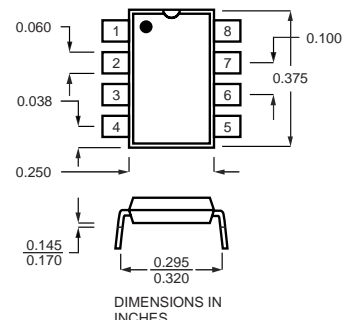
Standard package is SOT23 6 lead.
Other packages listed are optional. Contact factory regarding availability of optional packages.

NOTES:

1. Maximum rating for LS3550A, SOT23-6.

2. Absolute maximum ratings are limiting values above which serviceability may be impaired.

3. The reverse Base to Emitter voltage must never exceed -6.2 Volts. The reverse Base to Emitter current must never exceed -10µA.